Announcement and Call For Papers

The 19th International Symposium on Power Semiconductor Devices and ICs (ISPSD'07)

Jeju -Korea 27 to 31 May 2007

The 19th international Symposium on Power Semiconductor Devices and Integrated Circuits (ISPSD '07) will be the leading international forum in 2007 for presentation, review and discussion of the latest advances and developments in electronic devices and integrated circuits designed for energy transfer. ISPSD '07 will be held in beautiful Jeju Island, Korea. Conference will cover the most recent advances in the following subject areas:

Materials and Processes: Crystal Growth, Doping, Lifetime Control, Passivation, Characterization, Si, GaAs, SiC, GaN, Diamond.

Semiconductor CAD/Simulation: Process, Device, & Circuit Simulation, Layout, Verification Tools, Device Physics, DeviceFailure Modes, Reliability.

Discrete Power Devices: Diodes, MOSFETS, BJTs, IGBTs, Thyristors, High Power Devices, Intelligent Devices, PulsePower Devices, novel device structures in Si, SiC, GaAs and Diamond.

High Voltage and Low Voltage Power ICs: Isolation Techniques, SOI, Circuit Design, Device Technology, Monolithic vs. Hybrid.

RF and High Frequency Power Devices and Circuits: Devices for linear power amplification in the 1-10 GHz range in Si, GaAs, SiC, GaN and Diamond Devices for High Frequency Power Conversion.

Modules and Packaging: Novel Packaging Techniques, Stress and Thermal Simulation, Thermal Management, High Voltage and Power Dissipation Issues

Power Application: Automotive Electronics, Telecommunications, Display Drivers, Audio, Power Systems, Power Supply, EV, Traction, Elevators, Motor Control, Battery, Wind and Solar Systems, Power Factor Correction, EMC, Power Management.

PAPER SUBMISSION

Abstracts Must Clearly State: Purpose of work; how the work is differentiated from prior work; specific results and their significance with up-to-date reference

Electronic Submission: Prospective authors should visit the ISPSD'07 WEB Site: www.ISPSD07.org

Submit a PDF formatted paper through the above WEB site; including a one page text 500-word summary in English, headed by: Title, Author's names, Affiliations, Mailing address, Phone number, Fax number, and E-mail address, suggested area (Low Voltage and RF, High Voltage or Integrated Power) in which the abstract best fits, and two pages of supporting figures. Further instructions will be found at the site.

Deadline for Submission of the Summary: November 1, 2006

Notice of Acceptance: December 22, 2006

Deadline for Submission of the final manuscript: March 1, 2007

Sponsors: IEEE Electron Devices Society



The Institute of Electrical Engineers of Japan

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